TOSHIBA CMOS Digital Integrated Circuit Silicon Monolithic

TC7MP97FT, TC7MP97FK TC7MP98FT, TC7MP98FK

Low Voltage Triple Configurable Multiple Function Gate with 3.6 V Tolerant Inputs and Outputs

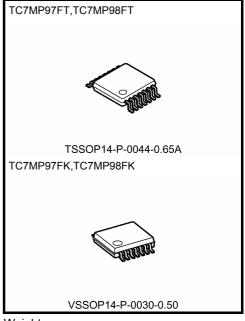
The TC7MP97,98 is a high performance CMOS multiple Function Gate which is guaranteed to operate from 1.2-V to 3.6-V. Designed for use in 1.5 V, 1.8 V, 2.5 V or 3.3 V systems, it achieves high speed operation while maintaining the CMOS low power dissipation.

It is also designed with over voltage tolerant inputs and outputs up to $3.6\ V$.

It independently consists of three circuits for Multiple Function Gate.

The output state is determined by seven patterns of 3-inputs. The user can choose the functions of Multiplexer, AND, OR, NAND, Schmitt Inverter, and Schmitt Buffer.

All inputs are equipped with protection circuits against static discharge.



Weight:

TSSOP14-P-0044-0.65A : 0.06 g(typ) VSSOP14-P-0030-0.50 : 0.02 g(typ)

Features

• Low-voltage operation :V_{CC} = 1.2 to 3.6 V

• High-speed operation : $t_{pd} = 8.5 \text{ ns (max) (V}_{CC} = 3.0 \text{ to } 3.6 \text{ V})$

 $t_{pd} = 12.0 \text{ ns (max) (V}_{CC} = 2.3 \text{ to } 2.7 \text{ V}$

• Output current : $|IOH|/IOL = \pm 8 \text{ mA (min)} (V_{CC} = 3.0 \text{ V})$

: |IOH|/I_{OL} = ±4 mA (min) (V_{CC} = 2.3 V) : |IOH|/I_{OL} = ±1.5 mA (min) (V_{CC} = 1.65 V)

1

• Latch-up performance : -300 mA

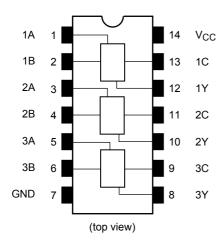
• ESD performance : Machine model $\geq \pm 200 \text{ V}$

Human body model ≥ ±2000 V

Package : VSSOP14 (US14),TSSOP14

Power-down protection is provided on all inputs and outputs

Pin Assignment (top view)



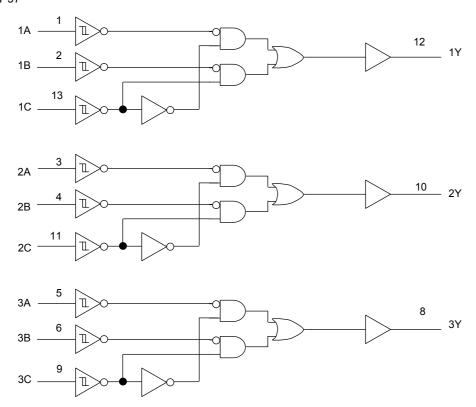
Truth Table

	INPUTS		OUT	ГРИТ
	INFUIS		TC7MP97	TC7MP98
Α	В	С	Υ	Υ
L	L	L	L	Н
L	L	Н	L	Н
L	Н	L	Н	L
L	Н	Н	L	Н
Н	L	L	L	Н
Н	L	Н	Н	L
Н	Н	L	Н	L
Н	Н	Н	Н	L

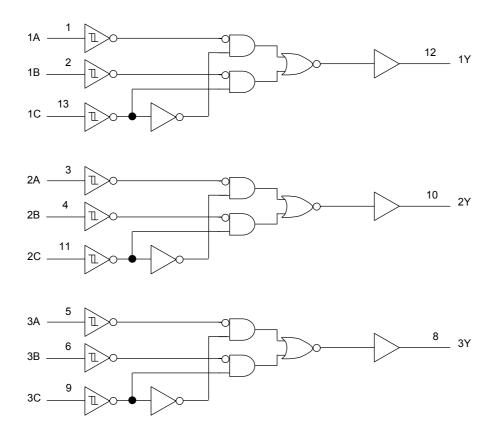


System Diagram

TC7MP97



TC7MP98





Logic configrations(1/2)

Function	Input Condition	TC7MP97 Logic symbol	TC7MP98 Logic symbol	FUNCTION TABLE
MP97 AND MP98 NAND	A=INPUT B=L-Level C=INPUT Y=OUTPUT	A Y	A Y	A B C Y 97 98 L L L L L H L L H L H
MP97 OR MP98 NOR	A=H-Level B=INPUT C=INPUT Y=OUTPUT	B Y	B Y	A B C Y 97 98 H L L L L H H L H L H H L H L H H H L H L
MP97 Schmitt INV+NOR or Schmitt INV+AND MP98 Schmitt INV+OR or Schmitt INV+NAND	A=L-Level B=INPUT C=INPUT Y=OUTPUT	B OR OR Y	B OR Y OR C Y	A B C Y 97 98 L L L L H L H L H L H L H L H L H
MP97 Schmitt INV+NAND or Schmitt INV+OR MP98 Schmitt INV+AND or Schmitt INV+AND	A=INPUT B=H-Level C=INPUT Y=OUTPUT	A OF Y OR A C T Y	A OF Y OR A C Y	A B C Y 97 98 L H L H L L H H L H H H L H L H H L H L
MP97 2 to 1 Selector MP98 2 to 1 Selector+INV	A=INPUT B=INPUT C=Select Y=OUTPUT	C A B Y	C A B Y	A B C Y 97 98 L L L L H L H L H L H L H L H H H L H L



Logic configrations(2/2)

Function	Input Condition	TC7MP97 Logic symbol	TC7MP98 Logic symbol	FUNCTION TABLE
MP97 Schmitt INV MP98 Schmitt Buffer	A=L-Level B=H-Level C=INPUT Y=OUTPUT	C Y	C Y	A B C Y 97 98 L H L H L L H H L H
MP97 Schmitt Buffer MP98 Schmitt INV	A=H-Level B=L-Level C=INPUT Y=OUTPUT	C Y	C Y	A B C Y 98 H L L L H H L H L
MP97 Schmitt Buffer MP98 Schmitt INV	A=L-Level B=INPUT C=L-Level Y=OUTPUT	В Y	B Y	A B C Y 97 98 L L L L H L H L H L
MP97 Schmitt Buffer MP98 Schmitt INV	A=H-Level B=INPUT C=L-Level Y=OUTPUT	В Y	В Y	A B C Y 97 98 H L L L H H H H L H L
MP97 Schmitt Buffer MP98 Schmitt INV	A=INPUT B=L-Level C=H-Level Y=OUTPUT	A Y	A Y	A B C Y 97 98 L L H L H H L H L L



Absolute Maximum Ratings (Note 1)

Characteristics	Symbol	Rating	Unit
Power supply voltage	V _{CC}	-0.5 to 4.6	V
DC input voltage	V _{IN}	-0.5 to 4.6	V
DC output voltage	V _{OUT}	-0.5 to 4.6 (Note 2)	٧
DC output voltage	VOUI	-0.5 to V _{CC} + 0.5 (Note 3)	
Input diode current	I _{IK}	-20	mA
Output diode current	lok	±20 (Note 4)	mA
DC output current	lout	±25	mA
Power dissipation	P _D	180	mW
DC V _{CC} /ground current	I _{CC} /I _{GND}	±25	mA
Storage temperature	T _{stg}	-65~150	°C

Note 1: Exceeding any of the absolute maximum ratings, even briefly, lead to deterioration in IC performance or even destruction.

Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings and the operating ranges.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

Note 2: $V_{CC} = 0 V$

Note 3: High or Low state. IOUT absolute ratiingmust be observed.

Note 4: $V_{OUT} < GND, V_{OUT} > V_{CC}$

Operating Ranges (Note 1)

Characteristics	Symbol	mbol Rating		
Supply voltage	V _{CC}	V _{CC} 1.2~3.6		
Input voltage	V _{IN}	-0.3~3.6	٧	
Output voltage	V _{OUT}	0~3.6 (Note 2)	٧	
Output voltage	VOU1	0~V _{CC} (Note 3)	V	
		±8.0 (Note 4)		
Output current	I _{OH} /I _{OL}	±4.0 (Note 5)	mA	
		±1.5 (Note 6)		
Operating temperature	T _{opr}	-40~85	°C	

Note 1: The operating ranges must be maintained to ensure the normal operation of the device.

Unused inputs must be tied to either VCC or GND.

6

Note 2: $V_{CC} = 0 V$

Note 3: High or low state

Note 4: $V_{CC} = 3.0 \sim 3.6 \text{ V}$

Note 5: $V_{CC} = 2.3 \sim 2.7 \text{ V}$

Note 6: $V_{CC} = 1.65 \sim 1.8 \text{ V}$



Electrical Characteristics

DC Characteristics ($Ta = -40 \text{ to } 85^{\circ}\text{C}$)

Characte	ristics	Symbol	Test C		Min	Max	Unit	
Ondraote		Cymbol	10010	onation	V _{CC} (V)	141111	Wax	Orint
					1.2		1.10	
				1.4		1.20		
	H-level	V _P			1.65		1.35	V
	i i-ievei	VP	_	_	2.3		1.70	V
					3.0		2.00	
Innut valtage					3.6		2.20	
Input voltage					1.2	0.10		
					1.4	0.20		
					1.65	0.30		1 ,,
	L-level	V _N	-	_	2.3	0.50		V
					3.0	0.70		
					3.6	0.80		
	1				1.2	0.2	0.9	
					1.4	0.2	0.9	V
						0.2	0.95	
Hysteresis voltage)	V _H	_		2.3	0.3	1.0	
						0.3	1.2	
					3.6	0.3	1.2	
				I _{OH} = -100 μA	1.2~1.3	Vcc - 0.1	_	
				I _{OH} = -500 μA	1.4~1.6	Vcc - 0.2	_	
	H-level	V _{OH}	V _{IN} = V _{IH} or V _{IL}	I _{OH} = -1.5 mA	1.65~1.95	Vcc - 0.3	_	
				I _{OH} = -4.0 mA	2.3~2.7	Vcc - 0.4	_	
0				$I_{OH} = -8.0 \text{ mA}$	3.0~3.6	2.40	_	1 ,,
Output voltage				I _{OL} = 100 μA	1.2~1.3	_	0.10	V
				I _{OL} = 500 μA	1.4~1.6	_	0.20	
	L-level	vel V_{OL} $V_{IN} = V_{IH}$ or V_{IL}		I _{OL} = 3.0 mA	1.65~1.95	_	0.25	
				I _{OL} = 4.0 mA	2.3~2.7	_	0.40	
			I +	I _{OL} = 8.0 mA	3.0~3.6	_	0.40	
Input leakage current		I _{IN}	V _{IN} = 0~3.6 V	1	1.2~3.6	_	±5.0	μА
Power-off leakage	current	loff	V _{IN} , V _{OUT} = 0~3.6	V	0	_	10.0	μА
Outros		1	V _{IN} = V _{CC} or GND		1.2~3.6	_	20.0	
Quiescent supply	current	Icc	V _{CC} ≤ V _{IN} ≤ 3.6 V		1.2~3.6	_	±20.0	μА
Increase in I _{CC} pe	er input	Δlcc	V _{IH} = V _{CC} - 0.6 V			_	750	1



AC Characteristics (Ta = -40 to 85° C, input: $t_r = t_f = 3.0$ ns)

Characteristics	Symbol	Symbol Test Condition		Min	Max	Unit
		E: 4 E: 0	V _{CC} (V)	1.0	21.0	
	t _{pLH}	Figure 1, Figure 2 $CL = 10pF$, $R_L = 1M \Omega$	2.5 ± 0.2	0.8	10.0	ns
	t _{pHL}	CL = TOPF, RL = TM 12	3.3 ± 0.3	0.6	7.0	
Propagation delay time	t _{pHL}	Figure 1, Figure 2 CL = 15pF, R_L = 1M Ω	1.8± 0.15	1.0	23.0	
(A, B,C-Y)			2.5 ± 0.2	0.8	11.0	ns
			3.3 ± 0.3	0.6	7.7	
		Figure 1, Figure 2 CL = 30pF, R_L = 1M Ω	1.8± 0.15	1.0	27.0	
			2.5 ± 0.2	0.8	12.0	ns
			3.3 ± 0.3	0.6	8.5	

Dynamic Switching Characteristics (Ta = 25°C, input: $t_r = t_f = 3.0$ ns, $C_L = 30$ pF)

Characteristics	Symbol	Test Condition			Unit
	,		V _{CC} (V)		
		$V_{IH} = 1.8 \text{ V}, V_{IL} = 0 \text{ V}$ (No	e) 1.8	0.25	
Quiet output maximum dynamic V _{OL}	V _{OLP}	$V_{IH} = 2.5 \text{ V}, V_{IL} = 0 \text{ V}$ (No	e) 2.5	0.6	V
		$V_{IH} = 3.3 \text{ V}, V_{IL} = 0 \text{ V}$ (No	e) 3.3	8.0	
		$V_{IH} = 1.8 \text{ V}, V_{IL} = 0 \text{ V}$ (No	e) 1.8	-0.25	
Quiet output minimum dynamic $V_{\mbox{OL}}$	V _{OLV}	$V_{IH} = 2.5 \text{ V}, V_{IL} = 0 \text{ V}$ (No	e) 2.5	-0.6	V
		$V_{IH} = 3.3 \text{ V}, V_{IL} = 0 \text{ V}$ (No	e) 3.3	-0.8	
		$V_{IH} = 1.8 \text{ V}, V_{IL} = 0 \text{ V}$ (No	e) 1.8	1.5	
Quiet output minimum dynamic V _{OH}	V _{OHV}	$V_{IH} = 2.5 \text{ V}, V_{IL} = 0 \text{ V}$ (No	e) 2.5	1.9	V
		$V_{IH} = 3.3 \text{ V}, V_{IL} = 0 \text{ V}$ (No	e) 3.3	2.2	

Note: Parameter guaranteed by design.

Capacitive Characteristics (Ta = 25°C)

Characteristics	Symbol		Test Condition	•	V _{CC} (V)	Тур.	Unit
Input capacitance	C _{IN}		_		1.8, 2.5, 3.3	6	pF
Power dissipation capacitance	C _{PD}	f _{IN} = 10 MHz		(Note)	1.8, 2.5, 3.3	30	pF

Note: C_{PD} is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load.

8

Average operating current can be obtained by the equation:

 $I_{CC (opr)} = C_{PD} \cdot V_{CC} \cdot f_{IN} + I_{CC}$

AC Test Circuit

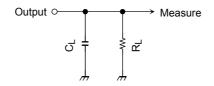
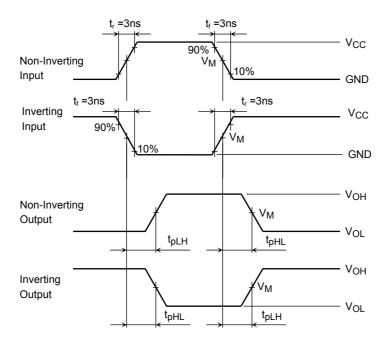


Figure 1

AC Waveform

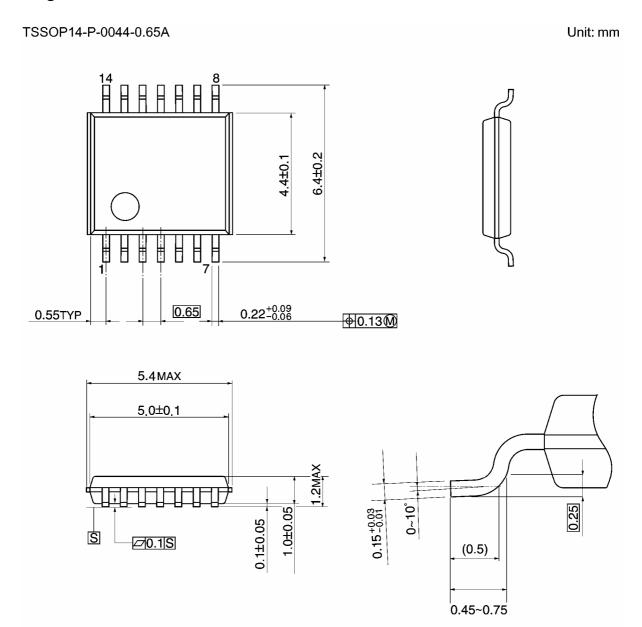


Symbol		V _{CC}	
Symbol	$3.3\pm0.3~\textrm{V}$	$2.5\pm0.2\textrm{V}$	1.8 V± 0.15 V
V _{IN}	V _{CC}	V _{CC}	V _{CC}
V _M	1.5 V	V _{CC} /2	V _{CC} /2

Figure 2 t_{pLH}, t_{pHL}



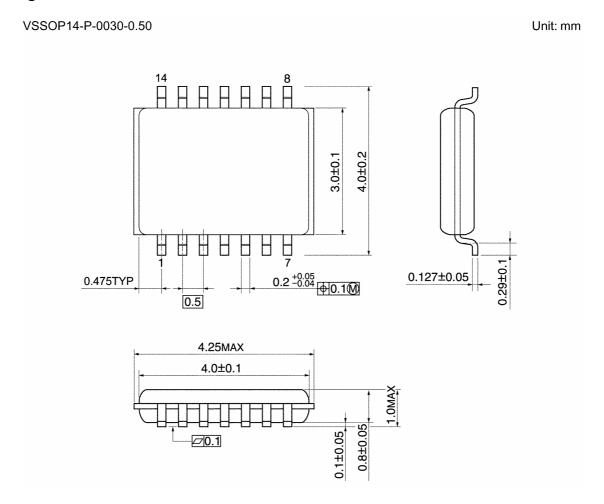
Package Dimensions



Weight: 0.06 g (typ.)



Package Dimensions



Weight: 0.02 g (typ.)

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